

# Ramdas Ram-Mohan

## List of Publications by Year in descending order

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18  
papers

170  
citations

1684188

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h-index

1125743

13  
g-index

19  
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19  
docs citations

19  
times ranked

168  
citing authors

#	ARTICLE	IF	CITATIONS
1	Non-asymptotic quantum scattering theory to design high-mobility lateral transition-metal dichalcogenide heterostructures. Journal of Applied Physics, 2022, 131, .	2.5	2
2	Exploration of the duality between generalized geometry and extraordinary magnetoresistance. Physical Review B, 2020, 101, .	3.2	1
3	Tuning spatial entanglement in interacting two-electron quantum dots. Physical Review B, 2020, 101, .	3.2	5
4	Effect of hydrostatic pressure on the electron-phonon scattering in GaAs. Journal of Applied Physics, 2019, 126, .	2.5	2
5	Electron scattering in quantum waveguides with sources and absorbers. I. Theoretical formalism. Journal of Applied Physics, 2019, 125, .	2.5	2
6	Electron scattering in quantum waveguides with sources and absorbers. II. Applications. Journal of Applied Physics, 2019, 125, .	2.5	3
7	Cavity electrostatics with Hermite interpolation: Role of symmetry and degeneracies. Journal of Applied Physics, 2018, 124, 213106.	2.5	4
8	Removal of accidental degeneracy in semiconductor quantum dots. Physical Review B, 2017, 96, .	3.2	1
9	Ternary diffusion path in terms of eigenvalues and eigenvectors. Philosophical Magazine, 2016, 96, 938-954.	1.6	5
10	Quantum mechanics on a Möbius ring: Energy levels, symmetry, optical transitions, and level splitting in a magnetic field. Physical Review B, 2012, 85, .	3.2	29
11	Energy spectrum of layered semiconductors in a magnetic field parallel to the layers: Voigt geometry. Physical Review B, 2010, 82, .	3.2	2
12	Size-dependent impurity activation energy in GaN nanowires. Applied Physics Letters, 2009, 94, 142102.	3.3	25
13	ELECTRONIC PARAMETER AND SUBBAND STRUCTURE VARIATIONS DUE TO AN EMBEDDED AlN POTENTIAL BARRIER LAYER IN Al <sub>0.3</sub> Ga <sub>0.7</sub> N/GaN HETEROSTRUCTURES. Surface Review and Letters, 2007, 14, 807-811.	1.1	0
14	Wavefunction engineering of layered semiconductors: theoretical foundations. Journal of Physics Condensed Matter, 2006, 18, R901-R917.	1.8	17
15	Wavefunction Engineering of Layered Quantum Semiconductor Structures: Recent Progress. Materials Research Society Symposia Proceedings, 2005, 891, 1.	0.1	0
16	The Schrödinger-Poisson self-consistency in layered quantum semiconductor structures. Journal of Applied Physics, 2004, 95, 3081-3092.	2.5	31
17	States confined in the barriers of type-III HgTe/CdTe superlattices. Journal of Electronic Materials, 1993, 22, 1103-1106.	2.2	4
18	Diagonal representation for the transfer-matrix method for obtaining electronic energy levels in layered semiconductor heterostructures. Physical Review B, 1992, 45, 1204-1212.	3.2	37